

ROHS COMPLIANT

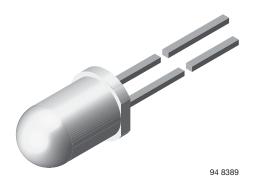
HALOGEN

FREE GREEN

(5-2008)

Vishay Semiconductors

High Power Infrared Emitting Diode, 940 nm, GaAlAs, MQW



DESCRIPTION

TSAL6402 is an infrared, 940 nm emitting diode in GaAlAs multi quantum well (MQW) technology with high radiant power and high speed molded in a blue-gray plastic package.

FEATURES

- Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- Peak wavelength: $\lambda_p r = 940 \text{ nm}$
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 25^{\circ}$
- Low forward voltage
- Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers

PRODUCT SUMMARY						
COMPONENT	l _e (mW/sr)	φ (deg)	λ _p (nm)	t _r (ns)		
TSAL6402	50	± 25	940	15		

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSAL6402	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

Note

• MOQ: minimum order quantity

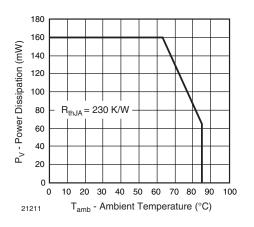
ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Reverse voltage		V _R	5	V		
Forward current		I _F	100	mA		
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA		
Surge forward current	t _p = 100 μs	I _{FSM}	1.5	A		
Power dissipation		Pv	160	mW		
Junction temperature		Тj	100	°C		
Operating temperature range		T _{amb}	-40 to +85	°C		
Storage temperature range		T _{stg}	-40 to +100	°C		
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C		
Thermal resistance junction-to-ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W		

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Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

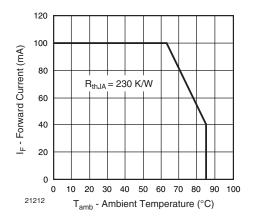


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F	-	1.35	1.6	V
	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V _F	-	2.2	-	V
Temperature coefficient of V_F	I _F = 1 mA	TK _{VF}	-	-1.8	-	mV/K
Reverse current	V _R = 5 V	I _R	-	-	10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj	-	40	-	pF
Radiant intensity	I _F = 100 mA, t _p = 20 ms	l _e	30	50	90	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	l _e	-	420	-	mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	фе	-	40	-	mW
Temperature coefficient of ϕ_{e}	I _F = 20 mA	ΤKφ _e	-	-0.6	-	%/K
Angle of half intensity		φ	-	± 25	-	deg
Peak wavelength	I _F = 100 mA	λρ	-	940	-	nm
Spectral bandwidth	I _F = 100 mA	Δλ	-	30	-	nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλρ	-	0.2	-	nm/K
Rise time	I _F = 100 mA	t _r	-	15	-	ns
Fall time	I _F = 100 mA	t _f	-	15	-	ns

TYPICAL DEDICATED CHARACTERISTICS ($T_{amb} = 25 \text{ °C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	BINNED GROUP	SYMBOL	MIN.	MAX.	UNIT
Radiant intensity	I _F = 100 mA, t _p = 20 ms	A 30	30	66	mW/sr	
	$t_{\rm F} = 100 {\rm mA}, t_{\rm p} = 20 {\rm ms}$	В	'e	54	90	11100/51

Note

• Each 4000 pcs box will contain a single group. The label on the box will indicate which binned group is in the box. A specific group cannot be ordered. Production shipments containing multiple boxes will likely include multiple groups. Please design accordingly



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BASIC CHARACTERISTICS (Tamb = 25 °C, unless otherwise specified)

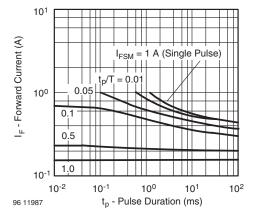


Fig. 3 - Pulse Forward Current vs. Pulse Duration

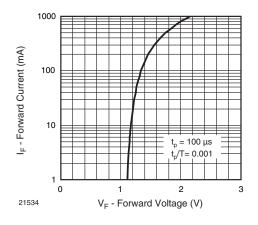


Fig. 4 - Forward Current vs. Forward Voltage

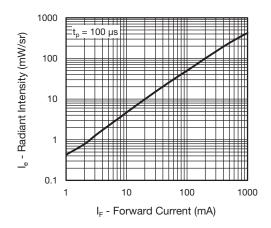


Fig. 5 - Radiant Intensity vs. Forward Current

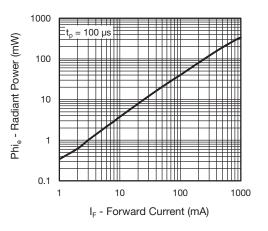


Fig. 6 - Radiant Power vs. Forward Current

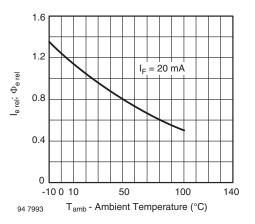


Fig. 7 - Relative Radiant Intensity / Power vs. Ambient Temperature

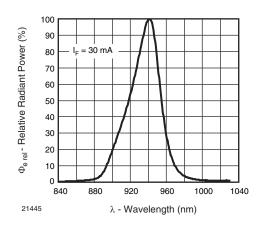


Fig. 8 - Relative Radiant Power vs. Wavelength

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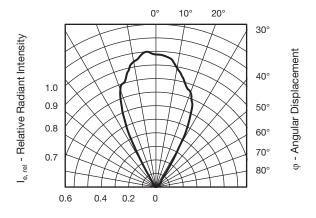
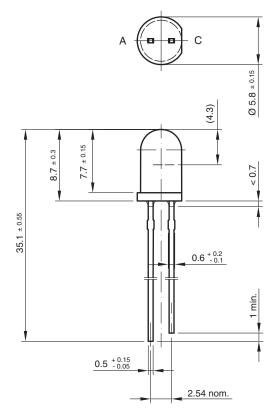
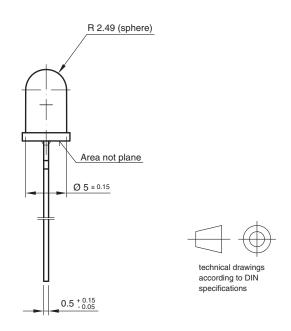


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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